High Current Transistors NPN Silicon

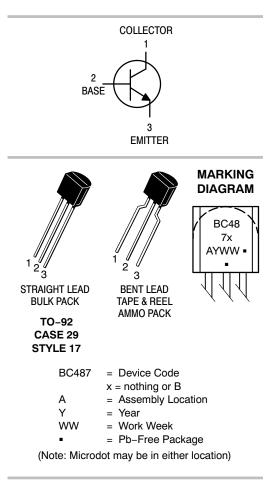
Features

• Pb-Free Packages are Available*



ON Semiconductor®

http://onsemi.com



ORDERING INFORMATION

Device	Package	Shipping [†]					
BC487	TO-92	5000 Units / Box					
BC487G	TO-92 (Pb-Free)	5000 Units / Box					
BC487B	TO-92	5000 Units / Box					
BC487BG	TO-92 (Pb-Free)	5000 Units / Box					
BC487BRL1	TO-92	2000/Tape & Reel					

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	60	Vdc
Collector – Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	۱ _C	0.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	R _{θJC}	83.3	°C/W

download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*For additional information on our Pb-Free strategy and soldering details, please

BC487, BC487B

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

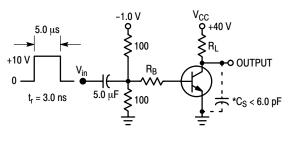
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	60	-	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	V _{(BR)CBO}	60	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 40 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	-	100	nAdc
ON CHARACTERISTICS*					

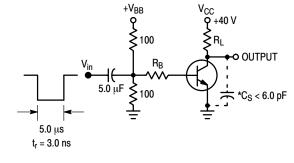
$\label{eq:loss} \begin{array}{ c c c } DC \ Current \ Gain \\ (I_C = 10 \ mAdc, \ V_{CE} = 2.0 \ Vdc) \\ (I_C = 100 \ mAdc, \ V_{CE} = 2.0 \ Vdc) \\ (I_C = 1.0 \ Adc, \ V_{CE} = 5.0 \ Vdc)^{\star} \end{array}$	BC487 BC487B	h _{FE}	40 60 160 15	- - 260 -	- 400 400 -	-
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$)		V _{CE(sat)}		0.2 0.3	0.5 -	Vdc
Base – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$) ⁽¹⁾		V _{BE(sat)}		0.85 0.9	1.2 -	Vdc
DYNAMIC CHARACTERISTICS						

Current–Gain – Bandwidth Product (I _C = 50 mAdc, V _{CE} = 2.0 Vdc, f = 100 MHz)	f _T	-	200	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	-	7.0	-	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ib}	-	50	-	pF

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.



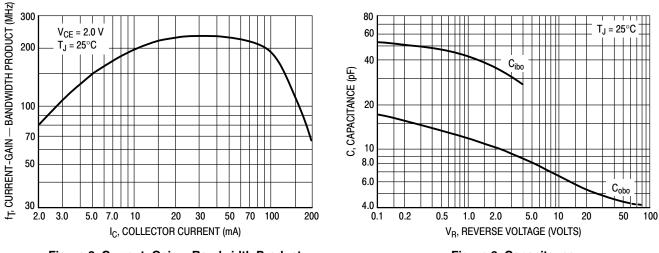




TURN-OFF TIME

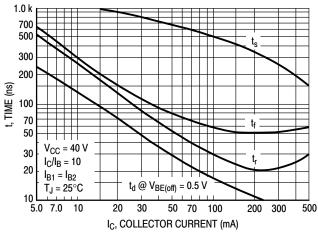
*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits











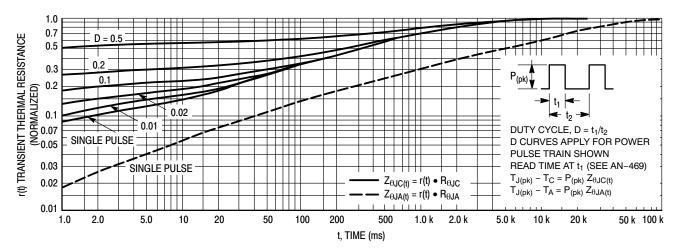


Figure 5. Thermal Response

BC487, BC487B

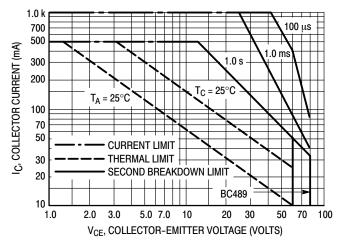
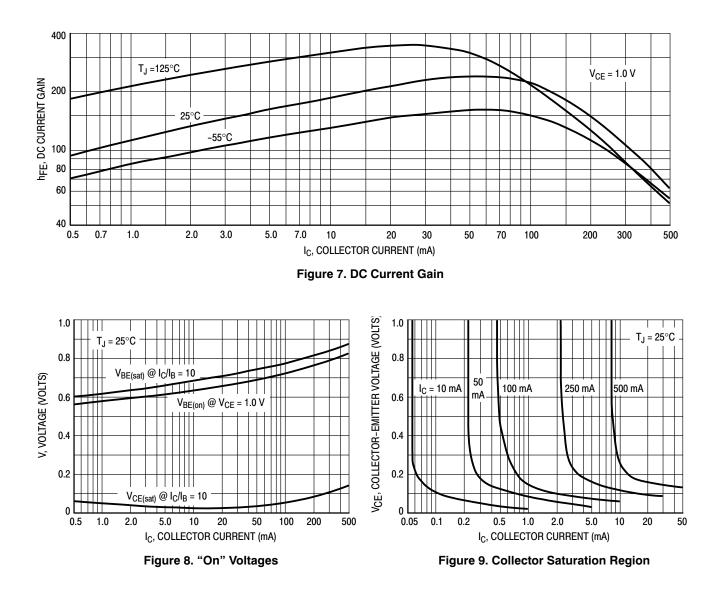
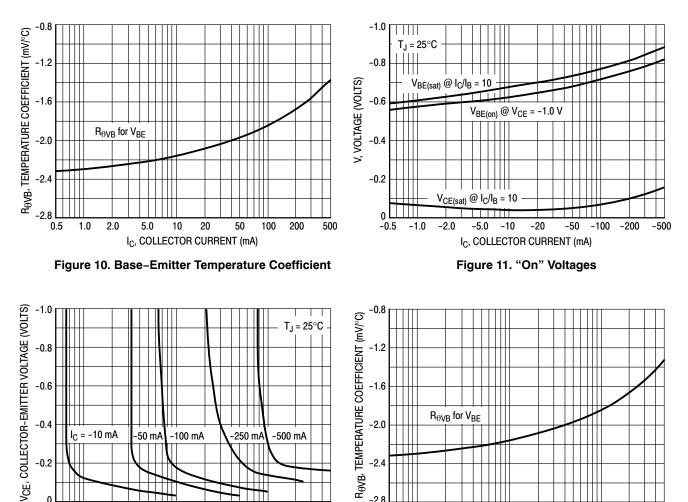


Figure 6. Active Region – Safe Operating Area



BC487, BC487B



-2.0

-2.4

-2.8

-0.5

-1.0

-2.0

-5.0

-10

-20

IC, COLLECTOR CURRENT (mA)

Figure 13. Base–Emitter Temperature Coefficient

-50

-100 -200

-500

-500 mA

-20

-50

-250 mA

Т

-10

-5.0

-0.4

-0.2

0

-0.05 -0.1 -0.2

I_C = -10 mA

-100 mA

-2.0

IB, BASE CURRENT (mA)

Figure 12. Collector Saturation Region

-50 mA

-0.5 -1.0

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** NOTES в STRAIGHT LEAD DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. **BULK PACK** CONTROLLING DIMENSION: INCH. 2 CONTROLLING DIMENSION INCR. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND 3. R 4 P BEYOND DIMENSION K MINIMUM INCHES MILLIMETERS SEATING DIM MIN MAX MIN MAX A 0.175 0.205 B 0.170 0.210 4.45 5.20 4.32 5.33 С 0.125 0.165 3.18 4.19 **D** 0.016 0.021 0.407 0.533 D G 0.045 0.055 1.15 1.39 Н 0.095 0.105 G 2.42 2.66 0.39 J 0.015 0.020 0.50 К 0.500 12.70 L 0.250 6.35 N 0.080 0.105 2.66 2.04 Ρ 0.100 2.54 SECTION X-X R 0.115 2.93 V 0.135 3.43 STYLE 17: PIN 1. COLLECTOR BASE EMITTER 2. 3. NOTES: **BENT LEAD** B DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. R 1. TAPE & REEL CONTROLLING DIMENSION: MILLIMETERS. 2. AMMO PACK CONTOUR OF PACKAGE BEYOND 3. DIMENSION R IS UNCONTROLLED. 4 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. Τ MILLIMETERS SEATING DIM MIN MAX κ 4.45 5.20 Α в 4.32 5.33 С 4.19 3.18 D 0.40 0.54 D G 2.40 2.80 J 0.39 0.50 G Κ 12.70 .1 Ν 2.04 2.66 Ρ 1.50 4.00 R 2.93 ٧ 3.43 SECTION X-X

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